



Welcome to E-XFL.COM

Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	18432
Number of I/O	71
Number of Gates	60000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-20°C ~ 85°C (TJ)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pn060-vq100

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Core Architecture

VersaTile

The proprietary IGLOO and ProASIC3 device architectures provide granularity comparable to gate arrays. The device core consists of a sea-of-VersaTiles architecture.

As illustrated in Figure 1-8, there are four inputs in a logic VersaTile cell, and each VersaTile can be configured using the appropriate flash switch connections:

- Any 3-input logic function
- Latch with clear or set
- D-flip-flop with clear or set
- Enable D-flip-flop with clear or set (on a 4th input)

VersaTiles can flexibly map the logic and sequential gates of a design. The inputs of the VersaTile can be inverted (allowing bubble pushing), and the output of the tile can connect to high-speed, very-long-line routing resources. VersaTiles and larger functions can be connected with any of the four levels of routing hierarchy.

When the VersaTile is used as an enable D-flip-flop, SET/CLR is supported by a fourth input. The SET/CLR signal can only be routed to this fourth input over the VersaNet (global) network. However, if, in the user's design, the SET/CLR signal is not routed over the VersaNet network, a compile warning message will be given, and the intended logic function will be implemented by two VersaTiles instead of one.

The output of the VersaTile is F2 when the connection is to the ultra-fast local lines, or YL when the connection is to the efficient long-line or very-long-line resources.

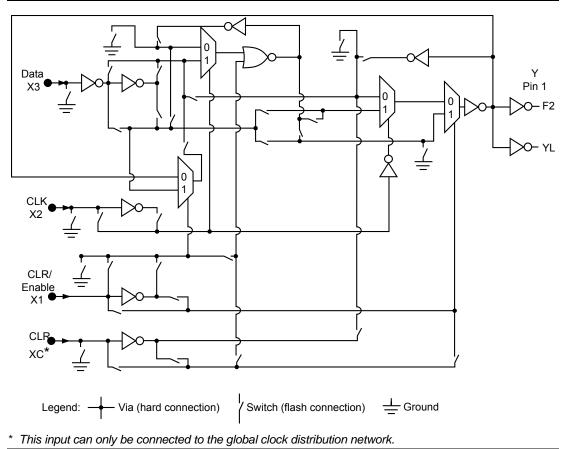


Figure 1-8 • Low Power Flash Device Core VersaTile



Global Resources in Low Power Flash Devices

Using Spines of Occupied Global Networks

When a signal is assigned to a global network, the flash switches are programmed to set the MUX select lines (explained in the "Clock Aggregation Architecture" section on page 45) to drive the spines of that network with the global net. However, if the global net is restricted from reaching into the scope of a spine, the MUX drivers of that spine are available for other high-fanout or critical signals (Figure 3-20).

For example, if you want to limit the CLK1_c signal to the left half of the chip and want to use the right side of the same global network for CLK2_c, you can add the following PDC commands:

define_region -name region1 -type inclusive 0 0 34 29
assign_net_macros region1 CLK1_c
assign_local_clock -net CLK2_c -type chip B2

Figure 3-20 • Design Example Using Spines of Occupied Global Networks

Conclusion

IGLOO, Fusion, and ProASIC3 devices contain 18 global networks: 6 chip global networks and 12 quadrant global networks. These global networks can be segmented into local low-skew networks called spines. The spines provide low-skew networks for the high-fanout signals of a design. These allow you up to 252 different internal/external clocks in an A3PE3000 device. This document describes the architecture for the global network, plus guidelines and methodologies in assigning signals to globals and spines.

Related Documents

User's Guides

IGLOO, ProASIC3, SmartFusion, and Fusion Macro Library Guide http://www.microsemi.com/soc/documents/pa3_libguide_ug.pdf

List of Changes

Date	Changes	Page
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	
	Notes were added where appropriate to point out that IGLOO nano and ProASIC3 nano devices do not support differential inputs (SAR 21449).	
	The "Global Architecture" section and "VersaNet Global Network Distribution" section were revised for clarity (SARs 20646, 24779).	31, 33
	The "I/O Banks and Global I/Os" section was moved earlier in the document, renamed to "Chip and Quadrant Global I/Os", and revised for clarity. Figure 3-4 • Global Connections Details, Figure 3-6 • Global Inputs, Table 3-2 • Chip Global Pin Name, and Table 3-3 • Quadrant Global Pin Name are new (SARs 20646, 24779).	35
	The "Clock Aggregation Architecture" section was revised (SARs 20646, 24779).	41
	Figure 3-7 • Chip Global Aggregation was revised (SARs 20646, 24779).	43
	The "Global Macro and Placement Selections" section is new (SARs 20646, 24779).	48
v1.4 (December 2008)	The "Global Architecture" section was updated to include 10 k devices, and to include information about VersaNet global support for IGLOO nano devices.	
	The Table 3-1 • Flash-Based FPGAs was updated to include IGLOO nano and ProASIC3 nano devices.	
	The "VersaNet Global Network Distribution" section was updated to include 10 k devices and to note an exception in global lines for nano devices.	
	Figure 3-2 • Simplified VersaNet Global Network (30 k gates and below) is new.	34
	The "Spine Architecture" section was updated to clarify support for 10 k and nano devices.	
	Table 3-4 • Globals/Spines/Rows for IGLOO and ProASIC3 Devices was updated to include IGLOO nano and ProASIC3 nano devices.	41
	The figure in the CLKBUF_LVDS/LVPECL row of Table 3-8 • Clock Macros was updated to change CLKBIBUF to CLKBUF.	46
v1.3 (October 2008)	A third bullet was added to the beginning of the "Global Architecture" section: In Fusion devices, the west CCC also contains a PLL core. In the two larger devices (AFS600 and AFS1500), the west and east CCCs each contain a PLL.	
	The "Global Resource Support in Flash-Based Devices" section was revised to include new families and make the information more concise.	32
	Table 3-4 • Globals/Spines/Rows for IGLOO and ProASIC3 Devices was updated to include A3PE600/L in the device column.	
	Table note 1 was revised in Table 3-9 • I/O Standards within CLKBUF to include AFS600 and AFS1500.	47
v1.2 (June 2008)	 The following changes were made to the family descriptions in Table 3-1 • Flash-Based FPGAs: ProASIC3L was updated to include 1.5 V. The number of PLLs for ProASIC3E was changed from five to six. 	32

The following table lists critical changes that were made in each revision of the chapter.

Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

Each group of control bits is assigned a specific location in the configuration shift register. For a list of the 81 configuration bits (C[80:0]) in the CCC and a description of each, refer to "PLL Configuration Bits Description" on page 90. The configuration register can be serially loaded with the new configuration data and programmed into the CCC using the following ports:

- SDIN: The configuration bits are serially loaded into a shift register through this port. The LSB of the configuration data bits should be loaded first.
- SDOUT: The shift register contents can be shifted out (LSB first) through this port using the shift operation.
- SCLK: This port should be driven by the shift clock.
- SSHIFT: The active-high shift enable signal should drive this port. The configuration data will be shifted into the shift register if this signal is HIGH. Once SSHIFT goes LOW, the data shifting will be halted.
- SUPDATE: The SUPDATE signal is used to configure the CCC with the new configuration bits when shifting is complete.

To access the configuration ports of the shift register (SDIN, SDOUT, SSHIFT, etc.), the user should instantiate the CCC macro in his design with appropriate ports. Microsemi recommends that users choose SmartGen to generate the CCC macros with the required ports for dynamic reconfiguration.

Users must familiarize themselves with the architecture of the CCC core and its input, output, and configuration ports to implement the desired delay and output frequency in the CCC structure. Figure 4-22 shows a model of the CCC with configurable blocks and switches.



Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

External Feedback Configuration

For certain applications, such as those requiring generation of PCB clocks that must be matched with existing board delays, it is useful to implement an external feedback, EXTFB. The Phase Detector of the PLL core will receive CLKA and EXTFB as inputs. EXTFB may be processed by the fixed System Delay element as well as the *M* divider element. The EXTFB option is currently not supported.

After setting all the required parameters, users can generate one or more PLL configurations with HDL or EDIF descriptions by clicking the **Generate** button. SmartGen gives the option of saving session results and messages in a log file:

Name	: test_pll
Family	: ProASIC3E
Output Format	: VHDL
Туре	: Static PLL
Input Freq(MHz)	: 10.000
CLKA Source	: Hardwired I/O
Feedback Delay Value Index	: 1
Feedback Mux Select	: 2
XDLY Mux Select	: No
Primary Freq(MHz)	: 33.000
Primary PhaseShift	: 0
Primary Delay Value Index	: 1
Primary Mux Select	: 4
Secondaryl Freq(MHz)	: 66.000
Use GLB	: YES
Use YB	: YES
GLB Delay Value Index	: 1
YB Delay Value Index	: 1
Secondaryl PhaseShift	: 0
Secondary1 Mux Select	: 4
Secondary2 Freq(MHz)	: 101.000
Use GLC	: YES
Use YC	: NO
GLC Delay Value Index	: 1
YC Delay Value Index	: 1
Secondary2 PhaseShift	: 0
Secondary2 Mux Select	: 4
Primary Clock frequency 33.333	
Primary Clock Phase Shift 0.000)
Primary Clock Output Delay from	
Secondaryl Clock frequency 66.6	67
Secondaryl Clock Phase Shift 0.	
Secondaryl Clock Global Output	
Secondaryl Clock Core Output De	_
-	-
Secondary2 Clock frequency 100.	000
Secondary2 Clock Phase Shift 0.	
Secondary2 Clock Global Output	
	-

Below is an example Verilog HDL description of a legal PLL core configuration generated by SmartGen:

module test_pll(POWERDOWN,CLKA,LOCK,GLA); input POWERDOWN, CLKA; output LOCK,GLA; Use quadrant global region assignments by finding the clock net associated with the CCC macro under the Nets tab and creating a quadrant global region for the net, as shown in Figure 4-33.

Figure 4-33 • Quadrant Clock Assignment for a Global Net

External I/O–Driven CCCs

The above-mentioned recommendation for proper layout techniques will ensure the correct assignment. It is possible that, especially with External I/O–Driven CCC macros, placement of the CCC macro in a desired location may not be achieved. For example, assigning an input port of an External I/O–Driven CCC near a particular CCC location does not guarantee global assignments to the desired location. This is because the clock inputs of External I/O–Driven CCCs can be assigned to any I/O location; therefore, it is possible that the CCC connected to the clock input will be routed to a location other than the one closest to the I/O location, depending on resource availability and placement constraints.

Clock Placer

The clock placer is a placement engine for low power flash devices that places global signals on the chip global and quadrant global networks. Based on the clock assignment constraints for the chip global and quadrant global clocks, it will try to satisfy all constraints, as well as creating quadrant clock regions when necessary. If the clock placer fails to create the quadrant clock regions for the global signals, it will report an error and stop Layout.

The user must ensure that the constraints set to promote clock signals to quadrant global networks are valid.

Cascading CCCs

The CCCs in low power flash devices can be cascaded. Cascading CCCs can help achieve more accurate PLL output frequency results than those achievable with a single CCC. In addition, this technique is useful when the user application requires the output clock of the PLL to be a multiple of the reference clock by an integer greater than the maximum feedback divider value of the PLL (divide by 128) to achieve the desired frequency.

For example, the user application may require a 280 MHz output clock using a 2 MHz input reference clock, as shown in Figure 4-34 on page 110.



FlashROM in Microsemi's Low Power Flash Devices

Programming and Accessing FlashROM

The FlashROM content can only be programmed via JTAG, but it can be read back selectively through the JTAG programming interface, the UJTAG interface, or via direct FPGA core addressing. The pages of the FlashROM can be made secure to prevent read-back via JTAG. In that case, read-back on these secured pages is only possible by the FPGA core fabric or via UJTAG.

A 7-bit address from the FPGA core defines which of the eight pages (three MSBs) is being read, and which of the 16 bytes within the selected page (four LSBs) are being read. The FlashROM content can be read on a random basis; the access time is 10 ns for a device supporting commercial specifications. The FPGA core will be powered down during writing of the FlashROM content. FPGA power-down during FlashROM programming is managed on-chip, and FPGA core functionality is not available during programming of the FlashROM. Table 5-2 summarizes various FlashROM access scenarios.

Access Mode	FlashROM Read	FlashROM Write
JTAG	Yes	Yes
UJTAG	Yes	No
FPGA core	Yes	No

Figure 5-6 shows the accessing of the FlashROM using the UJTAG macro. This is similar to FPGA core access, where the 7-bit address defines which of the eight pages (three MSBs) is being read and which of the 16 bytes within the selected page (four LSBs) are being read. Refer to the "UJTAG Applications in Microsemi's Low Power Flash Devices" section on page 297 for details on using the UJTAG macro to read the FlashROM.

Figure 5-7 on page 123 and Figure 5-8 on page 123 show the FlashROM access from the JTAG port. The FlashROM content can be read on a random basis. The three-bit address defines which page is being read or updated.

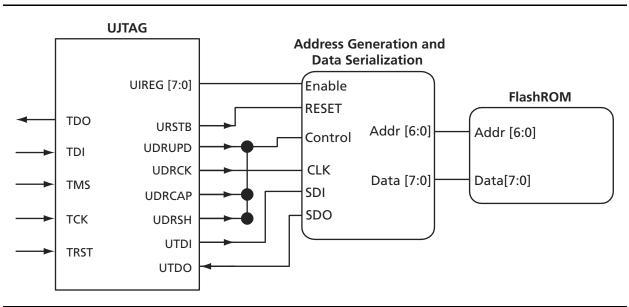


Figure 5-6 • Block Diagram of Using UJTAG to Read FlashROM Contents

FlashROM in Microsemi's Low Power Flash Devices

SmartGen allows you to generate the FlashROM netlist in VHDL, Verilog, or EDIF format. After the FlashROM netlist is generated, the core can be instantiated in the main design like other SmartGen cores. Note that the macro library name for FlashROM is UFROM. The following is a sample FlashROM VHDL netlist that can be instantiated in the main design:

```
library ieee;
use ieee.std_logic_1164.all;
library fusion;
entity FROM_a is
  port( ADDR : in std_logic_vector(6 downto 0); DOUT : out std_logic_vector(7 downto 0));
end FROM a;
architecture DEF_ARCH of FROM_a is
  component UFROM
    generic (MEMORYFILE:string);
    port(D00, D01, D02, D03, D04, D05, D06, D07 : out std_logic;
      ADDR0, ADDR1, ADDR2, ADDR3, ADDR4, ADDR5, ADDR6 : in std_logic := 'U') ;
  end component;
  component GND
    port( Y : out std_logic);
  end component;
signal U_7_PIN2 : std_logic ;
begin
  GND_1_net : GND port map(Y => U_7_PIN2);
  UFROM0 : UFROM
  generic map(MEMORYFILE => "FROM_a.mem")
  port map(DOO => DOUT(0), DO1 => DOUT(1), DO2 => DOUT(2), DO3 => DOUT(3), DO4 => DOUT(4),
    DO5 => DOUT(5), DO6 => DOUT(6), DO7 => DOUT(7), ADDR0 => ADDR(0), ADDR1 => ADDR(1),
    ADDR2 => ADDR(2), ADDR3 => ADDR(3), ADDR4 => ADDR(4), ADDR5 => ADDR(5),
    ADDR6 => ADDR(6));
```

end DEF_ARCH;

SmartGen generates the following files along with the netlist. These are located in the SmartGen folder for the Libero SoC project.

- 1. MEM (Memory Initialization) file
- 2. UFC (User Flash Configuration) file
- 3. Log file

The MEM file is used for simulation, as explained in the "Simulation of FlashROM Design" section on page 127. The UFC file, generated by SmartGen, has the FlashROM configuration for single or multiple devices and is used during STAPL generation. It contains the region properties and simulation values. Note that any changes in the MEM file will not be reflected in the UFC file. Do not modify the UFC to change FlashROM content. Instead, use the SmartGen GUI to modify the FlashROM content. See the "Programming File Generation for FlashROM Design" section on page 127 for a description of how the UFC file is used during the programming file generation. The log file has information regarding the file type and file location.

SRAM and FIFO Memories in Microsemi's Low Power Flash Devices

SRAM/FIFO Support in Flash-Based Devices

The flash FPGAs listed in Table 6-1 support SRAM and FIFO blocks and the functions described in this document.

Table 6-1 • Flash-Based FPGAs

Series	Family [*]	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3 ProASIC3 Low power, high-performance 1.5		Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM [®] Cortex [™] -M1 soft processors, and flash memory into a monolithic device

Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 6-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 6-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

SRAM and FIFO Memories in Microsemi's Low Power Flash Devices

Example of RAM Initialization

This section of the document presents a sample design in which a 4×4 RAM block is being initialized through the JTAG port. A test feature has been implemented in the design to read back the contents of the RAM after initialization to verify the procedure.

The interface block of this example performs two major functions: initialization of the RAM block and running a test procedure to read back the contents. The clock output of the interface is either the write clock (for initialization) or the read clock (for reading back the contents). The Verilog code for the interface block is included in the "Sample Verilog Code" section on page 151.

For simulation purposes, users can declare the input ports of the UJTAG macro for easier assignment in the testbench. However, the UJTAG input ports should not be declared on the top level during synthesis. If the input ports of the UJTAG are declared during synthesis, the synthesis tool will instantiate input buffers on these ports. The input buffers on the ports will cause Compile to fail in Designer.

Figure 6-10 shows the simulation results for the initialization step of the example design.

The CLK_OUT signal, which is the clock output of the interface block, is the inverted DR_UPDATE output of the UJTAG macro. It is clear that it gives sufficient time (while the TAP Controller is in the Data Register Update state) for the write address and data to become stable before loading them into the RAM block.

Figure 6-11 presents the test procedure of the example. The data read back from the memory block matches the written data, thus verifying the design functionality.

Figure 6-10 • Simulation of Initialization Step

Figure 6-11 • Simulation of the Test Procedure of the Example

ProASIC3 nano FPGA Fabric User's Guide

SmartGen enables the user to configure the desired RAM element to use either a single clock for read and write, or two independent clocks for read and write. The user can select the type of RAM as well as the width/depth and several other parameters (Figure 6-13).

Figure 6-13 • SmartGen Memory Configuration Interface

SmartGen also has a Port Mapping option that allows the user to specify the names of the ports generated in the memory block (Figure 6-14).

Figure 6-14 • Port Mapping Interface for SmartGen-Generated Memory

SmartGen also configures the FIFO according to user specifications. Users can select no flags, static flags, or dynamic flags. Static flag settings are configured using configuration flash and cannot be altered

DDR for Microsemi's Low Power Flash Devices

DDR Support in Flash-Based Devices

The flash FPGAs listed in Table 9-1 support the DDR feature and the functions described in this document.

Table 9-1 • Flash-Based FPGAs

Series	Family [*]	Description	
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology	
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards	
	IGLOO nano	The industry's lowest-power, smallest-size solution	
ProASIC3 ProASIC3 Low power, high-pe		Low power, high-performance 1.5 V FPGAs	
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards	
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities	
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology	
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L	
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L	
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications	
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM [®] Cortex™-M1 soft processors, and flash memory into a monolithic device	

Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 9-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 9-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

List of Changes

Date	Changes	Page
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
	Notes were added where appropriate to point out that IGLOO nano and ProASIC3 nano devices do not support differential inputs (SAR 21449).	N/A
v1.4 (December 2008)	IGLOO nano and ProASIC3 nano devices were added to Table 9-1 • Flash-Based FPGAs.	206
	The "I/O Cell Architecture" section was updated with information applicable to nano devices.	207
	The output buffer (OUTBUF_SSTL3_I) input was changed to D, instead of Q, in Figure 9-1 • DDR Support in Low Power Flash Devices, Figure 9-3 • DDR Output Register (SSTL3 Class I), Figure 9-6 • DDR Output Register (SSTL3 Class I), Figure 9-7 • DDR Tristate Output Register, LOW Enable, 8 mA, Pull-Up (LVTTL), and the output from the DDR_OUT macro was connected to the input of the TRIBUFF macro in Figure 9-7 • DDR Tristate Output Register, LOW Enable, 8 mA, Pull-Up (LVTTL).	205, 209, 212, 213
v1.3 (October 2008)	The "Double Data Rate (DDR) Architecture" section was updated to include mention of the AFS600 and AFS1500 devices.	205
	The "DDR Support in Flash-Based Devices" section was revised to include new families and make the information more concise.	206
 v1.2 The following changes were made to the family descriptions in Table 9-1 • Flash-Based FPGAs: ProASIC3L was updated to include 1.5 V. The number of PLLs for ProASIC3E was changed from five to six. 		206
v1.1 (March 2008)	The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	206

The following table lists critical changes that were made in each revision of the chapter.

Security in Low Power Flash Devices

Security Support in Flash-Based Devices

The flash FPGAs listed in Table 11-1 support the security feature and the functions described in this document.

Series	Family [*]	Description	
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology	
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards	
	IGLOO nano	The industry's lowest-power, smallest-size solution	
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities	
ProASIC3 ProASIC3 Low power, high-performance 1.5 V		Low power, high-performance 1.5 V FPGAs	
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards	
		Lowest-cost solution with enhanced I/O capabilities	
		ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology	
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L	
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L	
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications	
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM Cortex™-M1 soft processors, and flash memory into a monolithic device	

Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 11-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 11-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.



Security in Low Power Flash Devices

STAPL File with AES Encryption

- Does not contain AES key / FlashLock Key information
- · Intended for transmission through web or service to unsecured locations for programming

Conclusion

The new and enhanced security features offered in Fusion, IGLOO, and ProASIC3 devices provide stateof-the-art security to designs programmed into these flash-based devices. Microsemi low power flash devices employ the encryption standard used by NIST and the U.S. government—AES using the 128-bit Rijndael algorithm.

The combination of an on-chip AES decryption engine and FlashLock technology provides the highest level of security against invasive attacks and design theft, implementing the most robust and secure ISP solution. These security features protect IP within the FPGA and protect the system from cloning, wholesale "black box" copying of a design, invasive attacks, and explicit IP or data theft.

Term	Explanation	
Security Header programming file	Programming file used to program the FlashLock Pass Key and/or AES key into the device to secure the FPGA, FlashROM, and/or FBs.	
AES (encryption) key	128-bit key defined by the user when the AES encryption option is set in the Microsemi Designer software when generating the programming file.	
FlashLock Pass Key	128-bit key defined by the user when the FlashLock option is set in the Microsemi Desig software when generating the programming file.	
	The FlashLock Key protects the security settings programmed to the device. Once a device is programmed with FlashLock, whatever settings were chosen at that time are secure.	
FlashLock	The combined security features that protect the device content from attacks. These features are the following:	
	Flash technology that does not require an external bitstream to program the device	
	 FlashLock Pass Key that secures device content by locking the security settings and preventing access to the device as defined by the user 	
	AES key that allows secure, encrypted device reprogrammability	

Glossary

References

National Institute of Standards and Technology. "ADVANCED ENCRYPTION STANDARD (AES) Questions and Answers." 28 January 2002 (10 January 2005).

See http://csrc.nist.gov/archive/aes/index1.html for more information.

Programming Voltage (VPUMP) and VJTAG

Low-power flash devices support on-chip charge pumps, and therefore require only a single 3.3 V programming voltage for the VPUMP pin during programming. When the device is not being programmed, the VPUMP pin can be left floating or can be tied (pulled up) to any voltage between 0 V and 3.6 V². During programming, the target board or the FlashPro4/3/3X programmer can provide VPUMP. FlashPro4/3/3X is capable of supplying VPUMP to a single device. If more than one device is to be programmed using FlashPro4/3/3X on a given board, FlashPro4/3/3X should not be relied on to supply the VPUMP voltage. A FlashPro4/3/3X programmer is not capable of providing reliable VJTAG voltage. The board must supply VJTAG voltage to the device and the VJTAG pin of the programmer header must be connected to the device VJTAG pin. Microsemi recommends that VPUMP³ and VJTAG power supplies be kept separate with independent filtering capacitors rather than supplying them from a common rail. Refer to the "Board-Level Considerations" section on page 271 for capacitor requirements.

Low power flash device I/Os support a bank-based, voltage-supply architecture that simultaneously supports multiple I/O voltage standards (Table 12-2). By isolating the JTAG power supply in a separate bank from the user I/Os, low power flash devices provide greater flexibility with supply selection and simplify power supply and printed circuit board (PCB) design. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). Microsemi recommends that TCK be tied to GND through a 200 ohm to 1 Kohm resistor. This prevents a possible totempole current on the input buffer stage. For TDI, TMS, and TRST pins, the devices provide an internal nominal 10 Kohm pull-up resistor. During programming, all I/O pins, except for JTAG interface pins, are tristated and weakly pulled up to VCCI. This isolates the part and prevents the signals from floating. The JTAG interface pins are driven by the FlashPro4/3/3X during programming, including the TRST pin, which is driven HIGH.

Power Supply	Programming Mode	Current during Programming
VCC	1.2 V / 1.5 V	< 70 mA
VCCI	1.2 V / 1.5 V / 1.8 V / 2.5 V / 3.3 V (bank-selectable)	I/Os are weakly pulled up.
VJTAG	1.2 V / 1.5 V / 1.8 V / 2.5 V / 3.3 V	< 20 mA
VPUMP	3.15 V to 3.45 V	< 80 mA

Table	12-2 •	Power	Supplies
, and			Cappiloo

Note: All supply voltages should be at 1.5 V or higher, regardless of the setting during normal operation, except for IGLOO nano, where 1.2 V VCC and VJTAG programming is allowed.

Nonvolatile Memory (NVM) Programming Voltage

SmartFusion and Fusion devices need stable VCCNVM/VCCENVM³ (1.5 V power supply to the embedded nonvolatile memory blocks) and VCCOSC/VCCROSC⁴ (3.3 V power supply to the integrated RC oscillator). The tolerance of VCCNVM/VCCENVM is \pm 5% and VCCOSC/VCCROSC is \pm 5%.

Unstable supply voltage on these pins can cause an NVM programming failure due to NVM page corruption. The NVM page can also be corrupted if the NVM reset pin has noise. This signal must be tied off properly.

Microsemi recommends installing the following capacitors⁵ on the VCCNVM/VCCENVM and VCCOSC/VCCROSC pins:

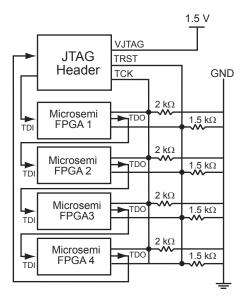
- Add one bypass capacitor of 10 μF for each power supply plane followed by an array of decoupling capacitors of 0.1 $\mu F.$
- Add one 0.1 µF capacitor near each pin.

^{2.} During sleep mode in IGLOO devices connect VPUMP to GND.

VPUMP has to be quiet for successful programming. Therefore VPUMP must be separate and required capacitors must be installed close to the FPGA VPUMP pin.

^{4.} VCCROSC is for SmartFusion.

^{5.} The capacitors cannot guarantee reliable operation of the device if the board layout is not done properly.



Note: TCK is correctly wired with an equivalent tie-off resistance of 500Ω , which satisfies the table for VJTAG of 1.5 V. The resistor values for TRST are not appropriate in this case, as the tie-off resistance of 375Ω is below the recommended minimum for VJTAG = 1.5 V, but would be appropriate for a VJTAG setting of 2.5 V or 3.3 V.

Figure 15-3 • Parallel Resistance on JTAG Chain of Devices

Advanced Boundary Scan Register Settings

You will not be able to control the order in which I/Os are released from boundary scan control. Testing has produced cases where, depending on I/O placement and FPGA routing, a 5 ns glitch has been seen on exiting programming mode. The following setting is recommended to prevent such I/O glitches:

- 1. In the FlashPro software, configure the advanced BSR settings for **Specify I/O Settings During Programming**.
- 2. Set the input BSR cell to **Low** for the input I/O.

UJTAG Applications in Microsemi's Low Power Flash Devices

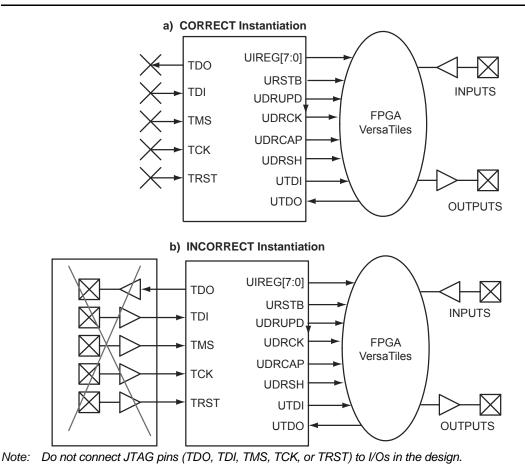


Figure 16-3 • Connectivity Method of UJTAG Macro

UJTAG Operation

There are a few basic functions of the UJTAG macro that users must understand before designing with it. The most important fundamental concept of the UJTAG design is its connection with the TAP Controller state machine.

TAP Controller State Machine

The 16 states of the TAP Controller state machine are shown in Figure 16-4 on page 301. The 1s and 0s, shown adjacent to the state transitions, represent the TMS values that must be present at the time of a rising TCK edge for a state transition to occur. In the states that include the letters "IR," the instruction register operates; in the states that contain the letters "DR," the test data register operates. The TAP Controller receives two control inputs, TMS and TCK, and generates control and clock signals for the rest of the test logic.

On power-up (or the assertion of TRST), the TAP Controller enters the Test-Logic-Reset state. To reset the controller from any other state, TMS must be held HIGH for at least five TCK cycles. After reset, the TAP state changes at the rising edge of TCK, based on the value of TMS.

17 – Power-Up/-Down Behavior of Low Power Flash Devices

Introduction

Microsemi's low power flash devices are flash-based FPGAs manufactured on a 0.13 μ m process node. These devices offer a single-chip, reprogrammable solution and support Level 0 live at power-up (LAPU) due to their nonvolatile architecture.

Microsemi's low power flash FPGA families are optimized for logic area, I/O features, and performance. IGLOO[®] devices are optimized for power, making them the industry's lowest power programmable solution. IGLOO PLUS FPGAs offer enhanced I/O features beyond those of the IGLOO ultra-low power solution for I/O-intensive low power applications. IGLOO nano devices are the industry's lowest-power cost-effective solution. ProASIC3[®]L FPGAs balance low power with high performance. The ProASIC3 family is Microsemi's high-performance flash FPGA solution. ProASIC3 nano devices offer the lowest-cost solution with enhanced I/O capabilities.

Microsemi's low power flash devices exhibit very low transient current on each power supply during power-up. The peak value of the transient current depends on the device size, temperature, voltage levels, and power-up sequence.

The following devices can have inputs driven in while the device is not powered:

- IGLOO (AGL015 and AGL030)
- IGLOO nano (all devices)
- IGLOO PLUS (AGLP030, AGLP060, AGLP125)
- IGLOOe (AGLE600, AGLE3000)
- ProASIC3L (A3PE3000L)
- ProASIC3 (A3P015, A3P030)
- ProASIC3 nano (all devices)
- ProASIC3E (A3PE600, A3PE1500, A3PE3000)
- Military ProASIC3EL (A3PE600L, A3PE3000L, but not A3P1000)
- RT ProASIC3 (RT3PE600L, RT3PE3000L)

The driven I/Os do not pull up power planes, and the current draw is limited to very small leakage current, making them suitable for applications that require cold-sparing. These devices are hot-swappable, meaning they can be inserted in a live power system.¹

^{1.} For more details on the levels of hot-swap compatibility in Microsemi's low power flash devices, refer to the "Hot-Swap Support" section in the I/O Structures chapter of the FPGA fabric user's guide for the device you are using.

Power-Up/-Down Behavior of Low Power Flash Devices

Figure 17-3 • I/O State when VCCI Is Powered before VCC

Power-Up to Functional Time

At power-up, device I/Os exit the tristate mode and become functional once the last voltage supply in the power-up sequence (VCCI or VCC) reaches its functional activation level. The power-up–to–functional time is the time it takes for the last supply to power up from zero to its functional level. Note that the functional level of the power supply during power-up may vary slightly within the specification at different ramp-rates. Refer to Table 17-2 for the functional level of the voltage supplies at power-up.

Typical I/O behavior during power-up-to-functional time is illustrated in Figure 17-2 on page 311 and Figure 17-3.

Device	VCC Functional Activation Level (V)	VCCI Functional Activation Level (V)
ProASIC3, ProASIC3 nano, IGLOO, IGLOO nano, IGLOO PLUS, and ProASIC3L devices running at VCC = 1.5 V*	0.85 V ± 0.25 V	0.9 V ± 0.3 V
IGLOO, IGLOO nano, IGLOO PLUS, and ProASIC3L devices running at VCC = 1.2 V*	0.85 V ± 0.2 V	0.9 V ± 0.15 V

Table 17-2 • Power-Up Functional Activation Levels for VCC and VCCI

Note: *V5 devices will require a 1.5 V VCC supply, whereas V2 devices can utilize either a 1.2 V or 1.5 V VCC.

Microsemi's low power flash devices meet Level 0 LAPU; that is, they can be functional prior to V_{CC} reaching the regulated voltage required. This important advantage distinguishes low power flash devices from their SRAM-based counterparts. SRAM-based FPGAs, due to their volatile technology, require hundreds of milliseconds after power-up to configure the design bitstream before they become functional. Refer to Figure 17-4 on page 313 and Figure 17-5 on page 314 for more information.